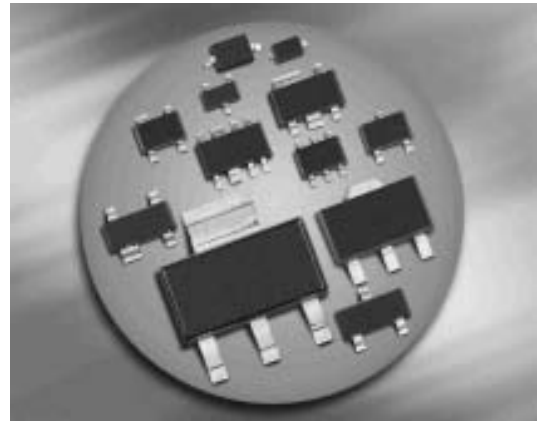
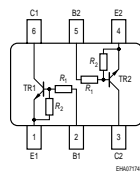
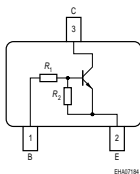


NPN Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1=2.2\text{ k}\Omega$, $R_2=47\text{ k}\Omega$)
- BCR108S: Two internally isolated transistors with good matching in one multichip package
- BCR108S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101


BCR108/F
BCR108T/W
BCR108S


Type	Marking	Pin Configuration						Package
BCR108	WHs	1=B	2=E	3=C	-	-	-	SOT23
BCR108F	WHs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR108S	WHs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BCR108W	WHs	1=B	2=E	3=C	-	-	-	SOT323

¹Pb-containing package may be available upon special request

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	20	
Input reverse voltage	$V_{i(rev)}$	5	
Collector current	I_C	100	mA
Total power dissipation- BCR108, $T_S \leq 102^\circ\text{C}$ BCR108F, $T_S \leq 128^\circ\text{C}$ BCR108S, $T_S \leq 115^\circ\text{C}$ BCR108W, $T_S \leq 124^\circ\text{C}$	P_{tot}	200 250 250 250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR108		≤ 240	
BCR108F		≤ 90	
BCR108S		≤ 140	
BCR108W		≤ 105	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

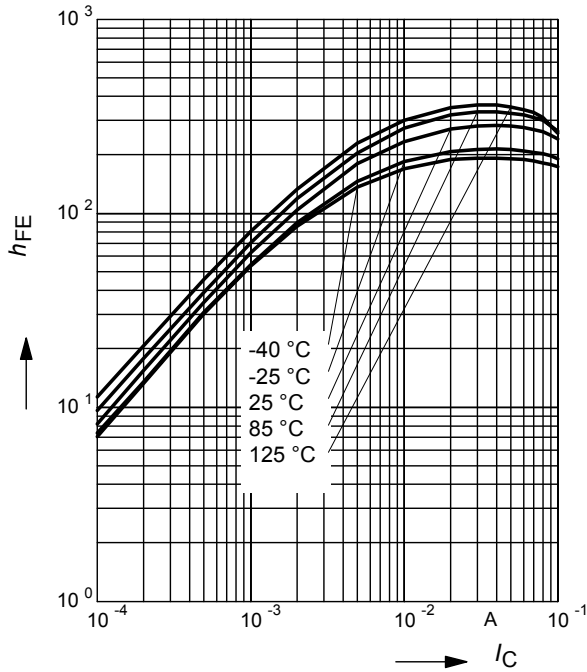
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 5 \text{ V}, I_C = 0$	I_{EBO}	-	-	164	μA
DC current gain ¹⁾ $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	h_{FE}	70	-	-	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(off)}$	0.4	-	0.8	
Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0.3 \text{ V}$	$V_{i(on)}$	0.5	-	1.1	
Input resistor	R_1	1.5	2.2	2.9	$\text{k}\Omega$
Resistor ratio	R_1/R_2	0.042	0.047	0.052	-
AC Characteristics					
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ MHz}$	f_T	-	170	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{cb}	-	2	-	pF

¹Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)

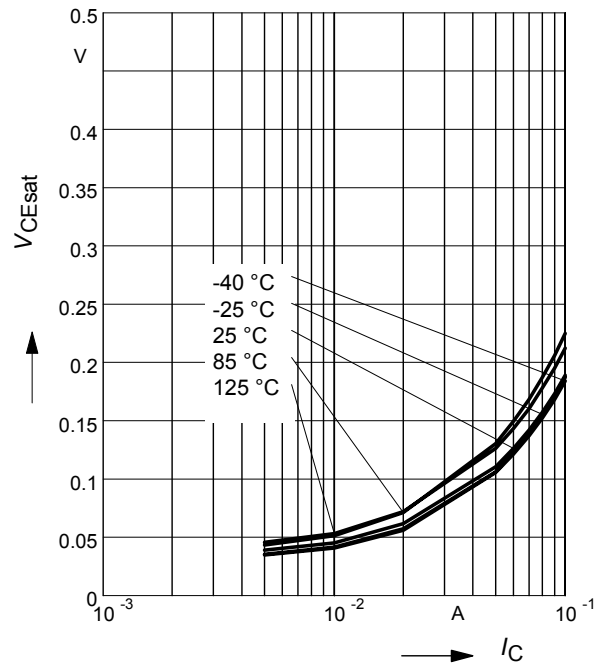
$T_A = \text{Parameter}$



Collector-emitter saturation voltage

$V_{CEsat} = f(I_C), I_C/I_B = 20$

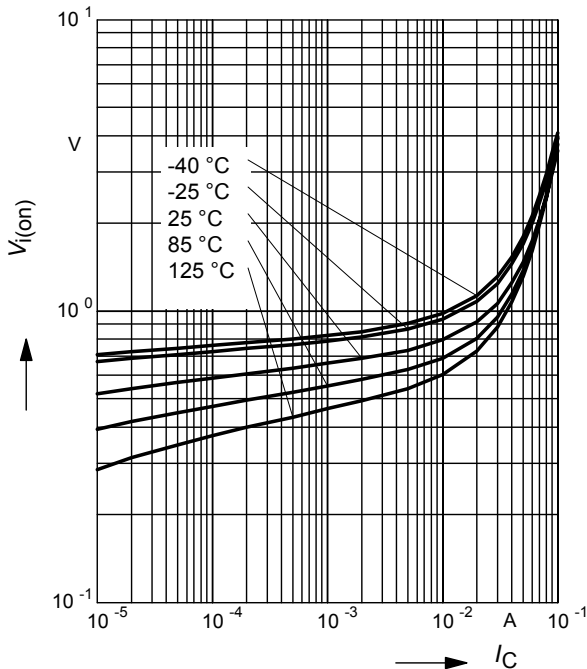
$T_A = \text{Parameter}$



Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$ (common emitter configuration)

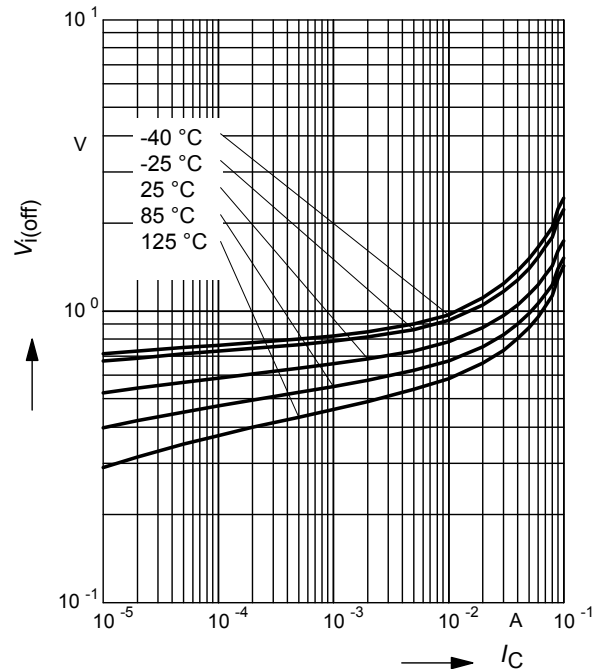
$T_A = \text{Parameter}$



Input off voltage $V_{i(off)} = f(I_C)$

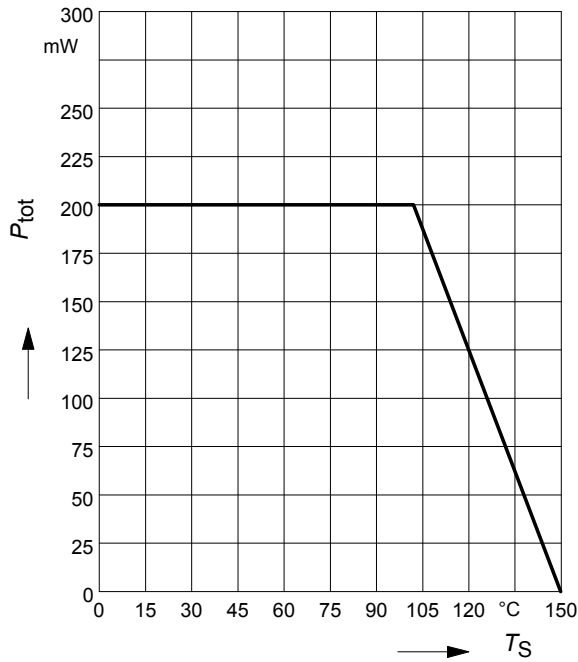
$V_{CE} = 5V$ (common emitter configuration)

$T_A = \text{Parameter}$



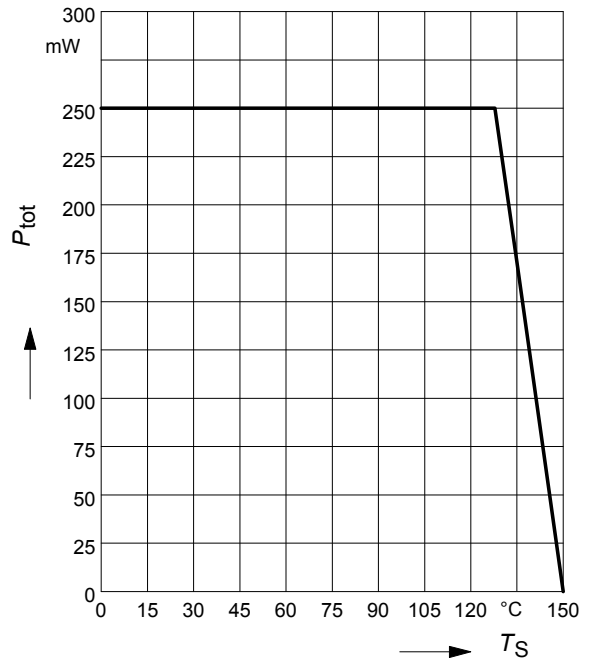
Total power dissipation $P_{tot} = f(T_S)$

BCR108



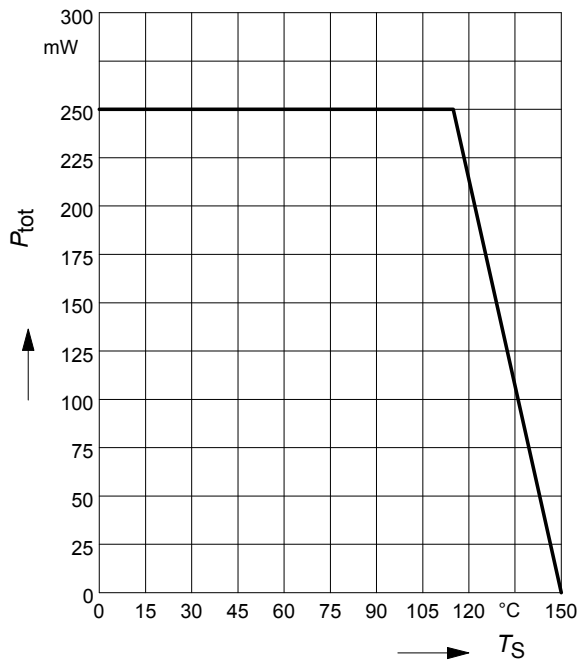
Total power dissipation $P_{tot} = f(T_S)$

BCR108F



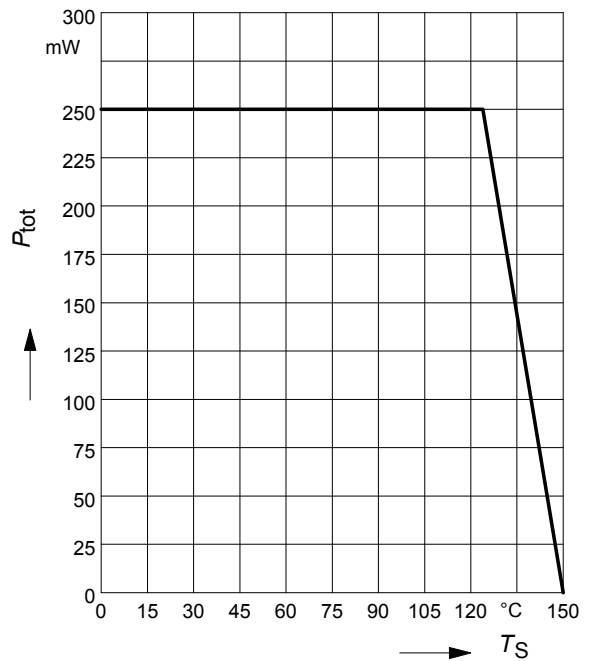
Total power dissipation $P_{tot} = f(T_S)$

BCR108S



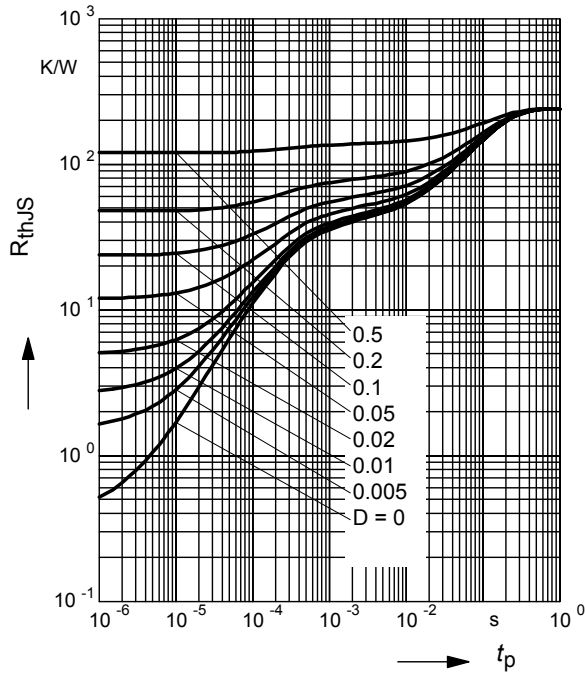
Total power dissipation $P_{tot} = f(T_S)$

BCR108W



Permissible Pulse Load $R_{thJS} = f(t_p)$

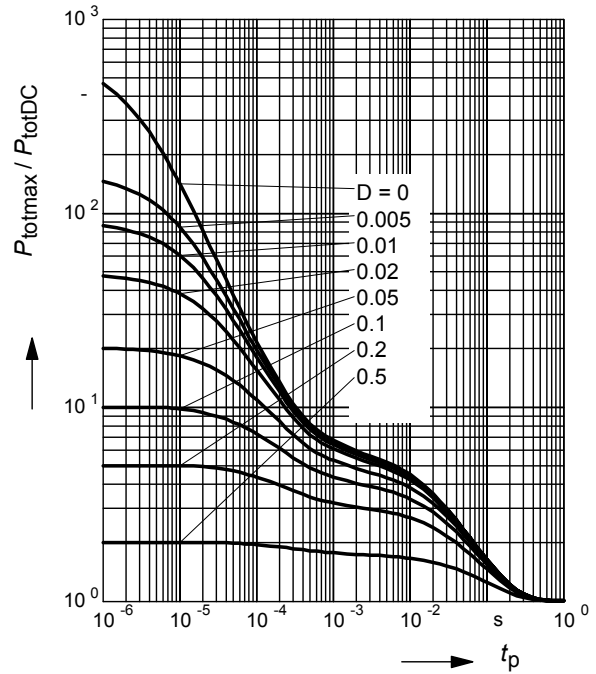
BCR108



Permissible Pulse Load

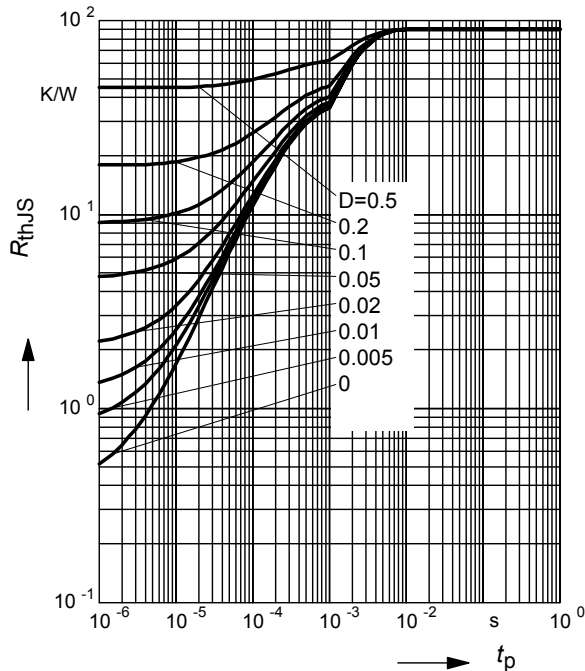
$P_{totmax}/P_{totDC} = f(t_p)$

BCR108



Permissible Puls Load $R_{thJS} = f(t_p)$

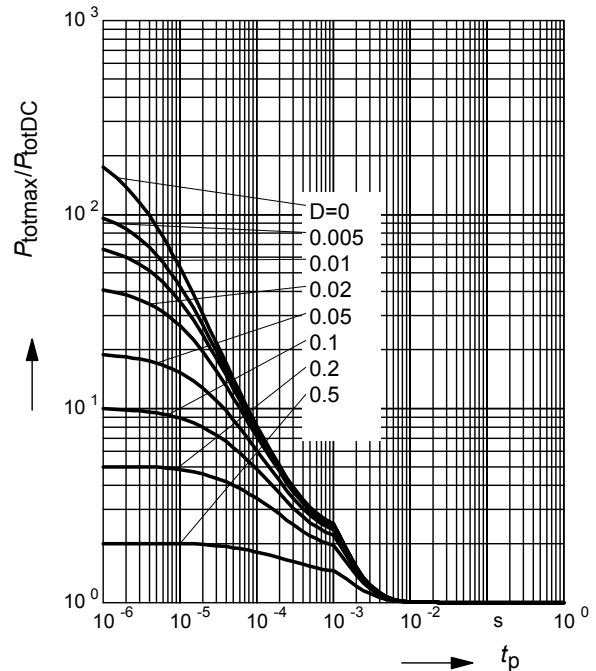
BCR108F



Permissible Pulse Load

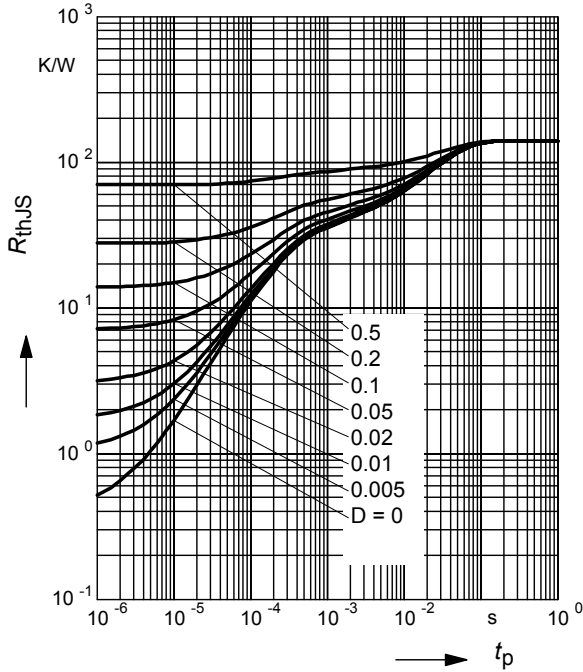
$P_{totmax}/P_{totDC} = f(t_p)$

BCR108F



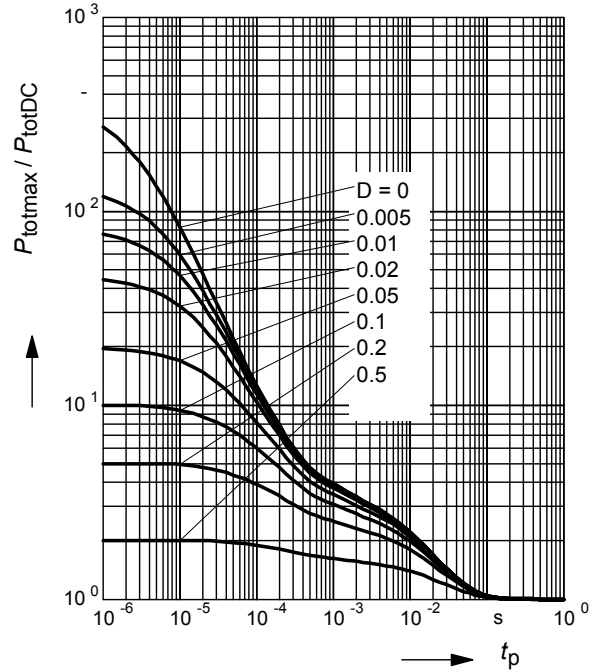
Permissible Puls Load $R_{thJS} = f(t_p)$

BCR108S



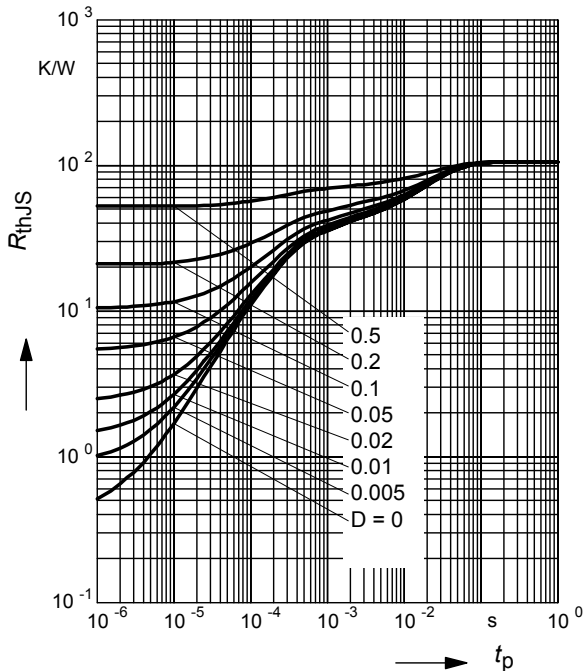
Permissible Pulse Load $P_{totmax}/P_{totDC} = f(t_p)$

BCR108S



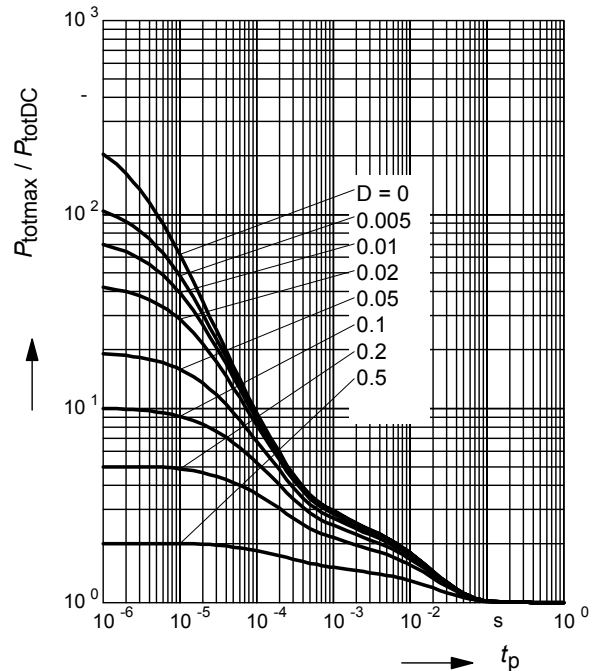
Permissible Puls Load $R_{thJS} = f(t_p)$

BCR108W

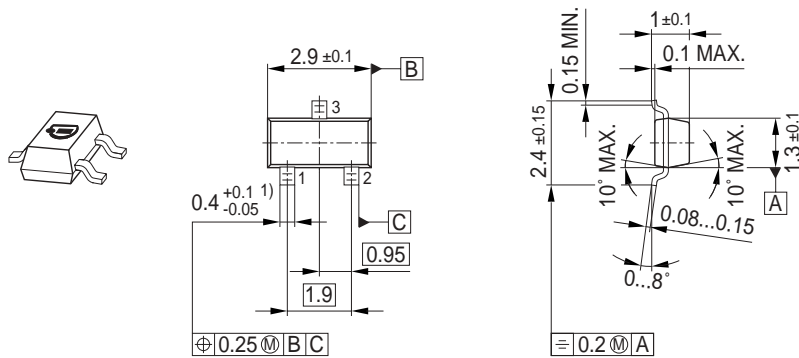


Permissible Pulse Load $P_{totmax}/P_{totDC} = f(t_p)$

BCR108W

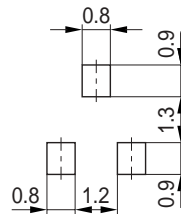


Package Outline

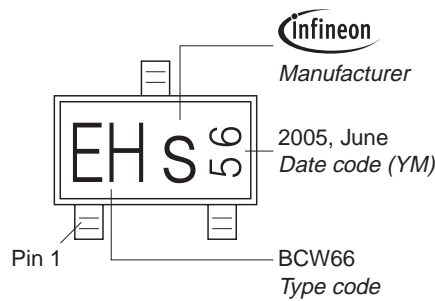


1) Lead width can be 0.6 max. in dambar area

Foot Print

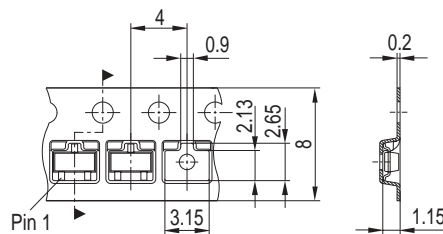


Marking Layout (Example)

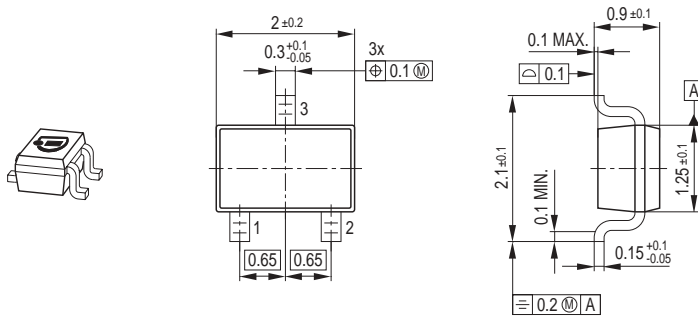


Standard Packing

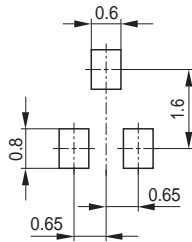
Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel



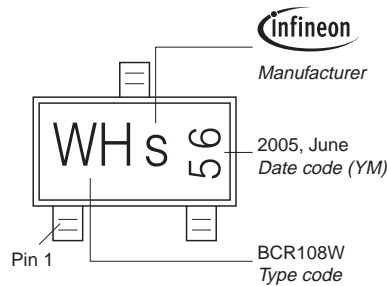
Package Outline



Foot Print

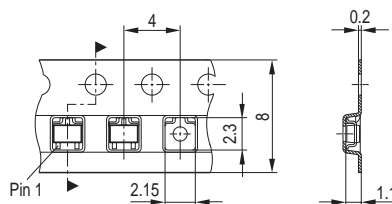


Marking Layout (Example)

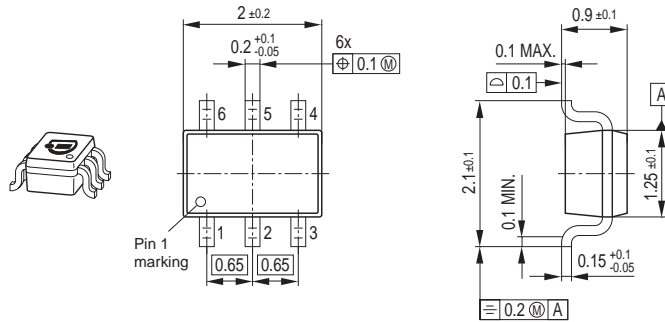


Standard Packing

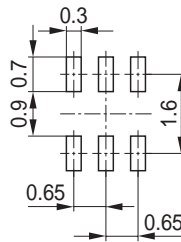
Reel $\varnothing 180 \text{ mm}$ = 3.000 Pieces/Reel
 Reel $\varnothing 330 \text{ mm}$ = 10.000 Pieces/Reel



Package Outline

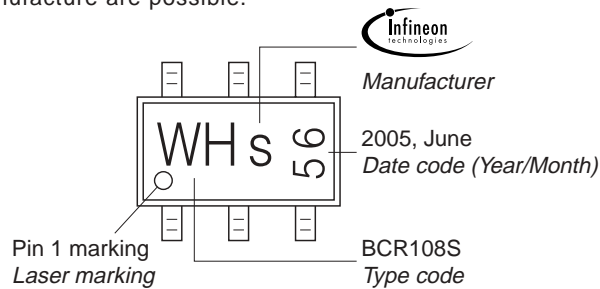


Foot Print



Marking Layout (Example)

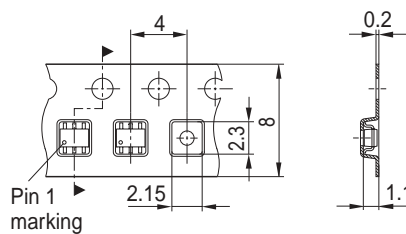
Small variations in positioning of Date code, Type code and Manufacture are possible.



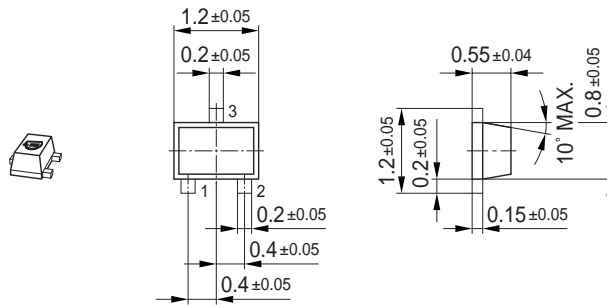
Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

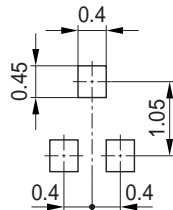
For symmetric types no defined Pin 1 orientation in reel.



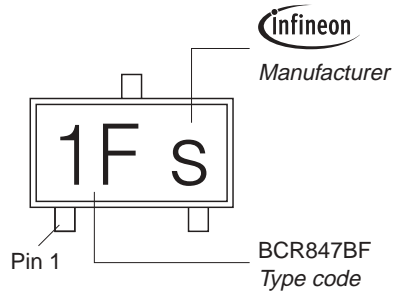
Package Outline



Foot Print

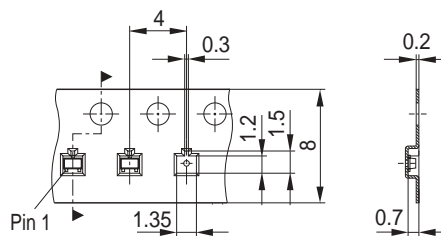


Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



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